Introduction to Nanophysics

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2/2014

What is the size for a “nano” ?

One (nm) equals to 1/1000000000 (10^{-9}) meter

10^{-3} m , **Macro**

10^{-6} m , **Micro**

10^{-9} m , **Meso**

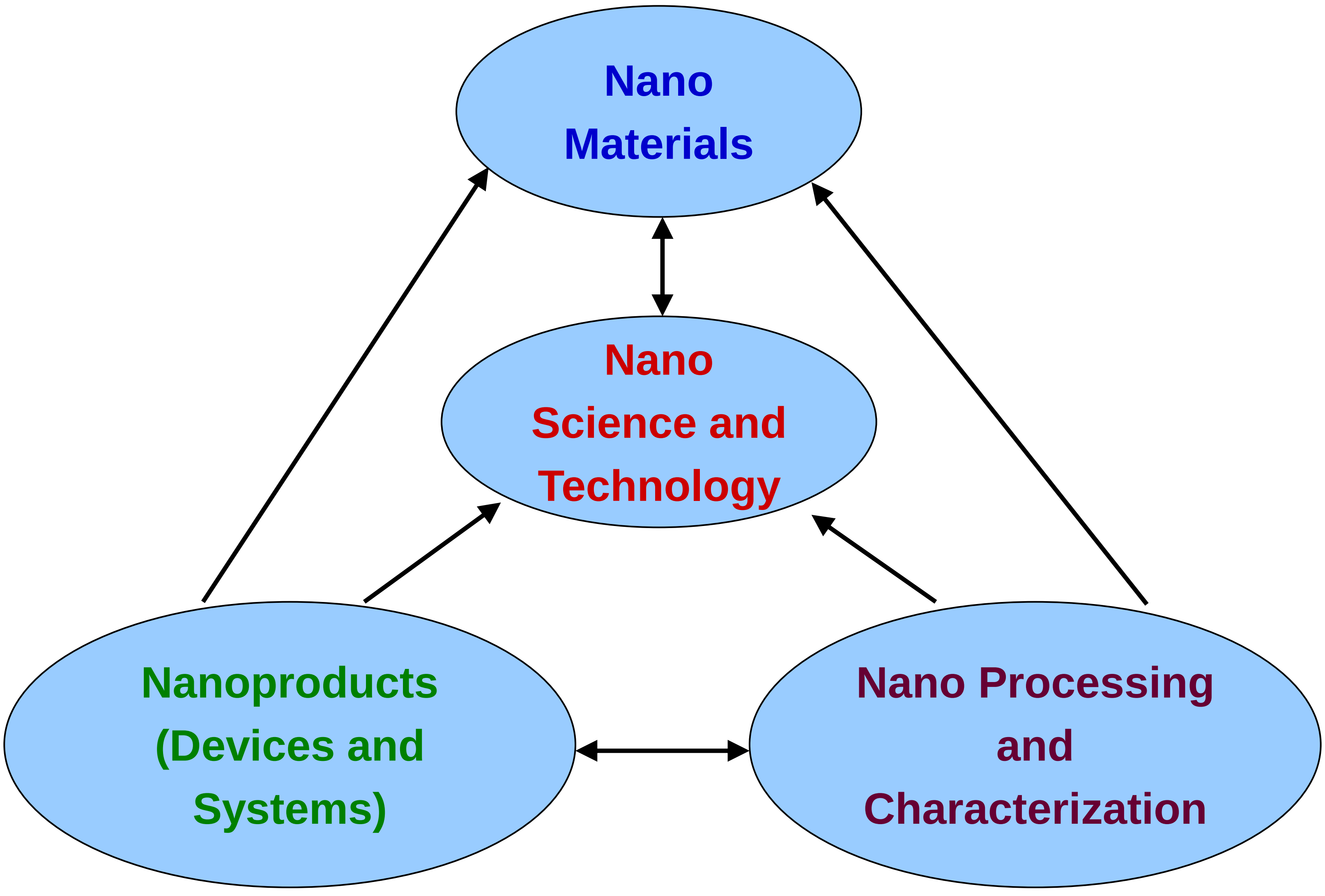
R. Feymann Already Knew about this !

“ There’s plenty of room at the bottom ! ” in 1959.

Physicists noticed the "Nano " as early as .....

- 4th Century, Roman glassmaker: the color of glasses can be changed by mixing in metal particles
- In 1883, Films containing silver halides for photography were invented by George Eastman, founder of Koda.k
- 1908, Gustay Mie first provided the explanation of the size dependence of color.
- Vision from Feynman in 1959: "There is plenty room at the bottom", and also recognized there are plenty of nature-given nanostructures in biological systems.
- 1950-1960, small metal particles were investigated by physicists.
- 1957, Ralph Landauer realized the importance of quantum mechanics plays in devices with small scales.
- Before 1997 => **mesoscopic** (or low dimensional) physics : quantum dots, wells, wires…..are known already.

Major Topics of Nanoscience and Technology



What is the Nano Technology?

- **Science and Technology Down scaling to size under100 nm:**

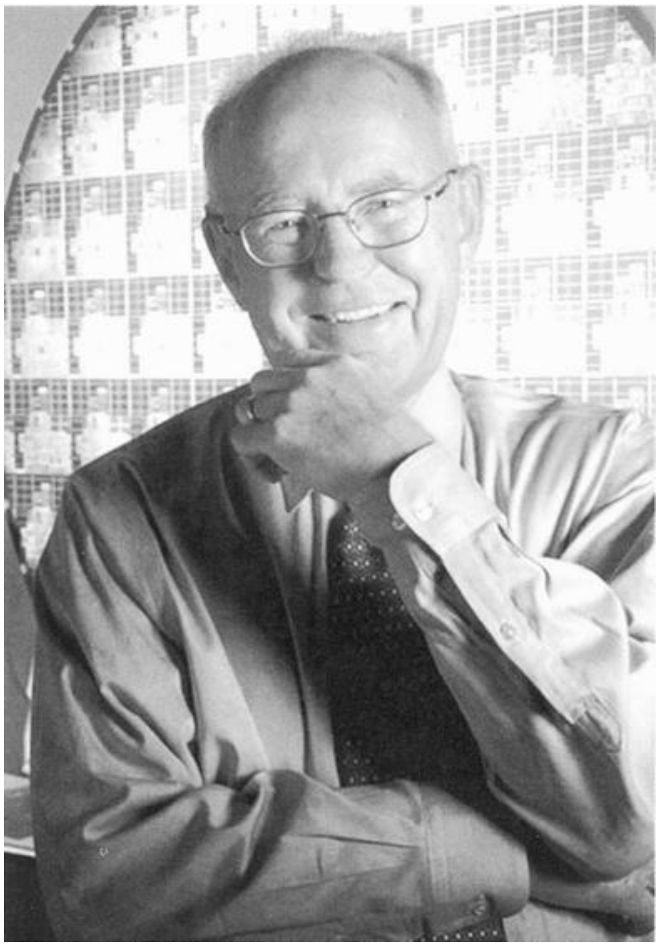
  Via the "Top-down" lithographic pattering.
  -- Moore's law !

- **Manipulate the atomic and molecular structures："Bottom-up" nano materials, growth and assembly.**

  Feymann: There's plenty of room at the bottom

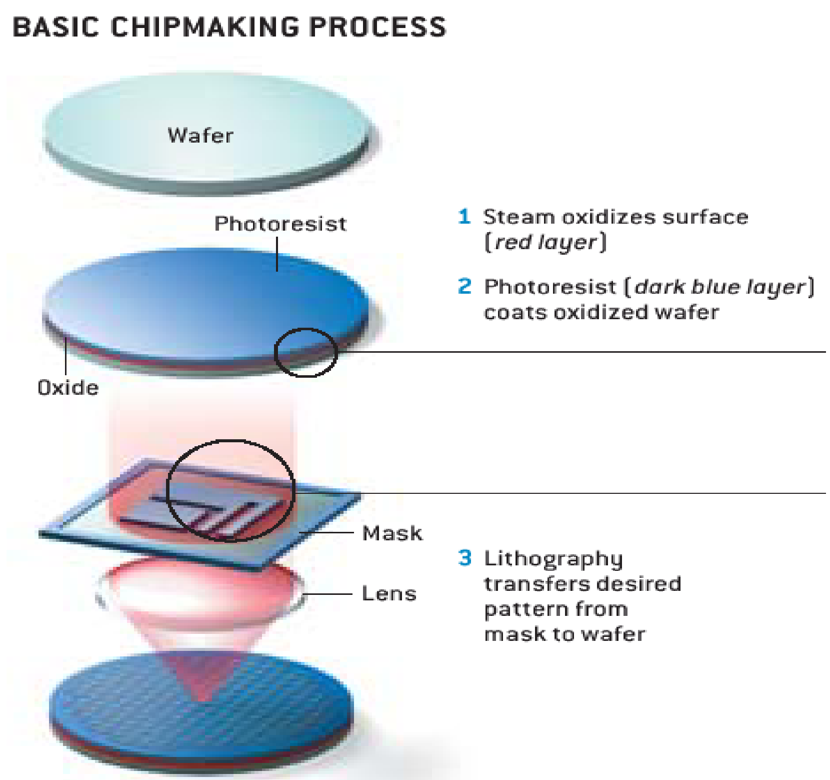
Major Driving Force pushing for Nano

Is due to the bottle neck met in Microelectronics



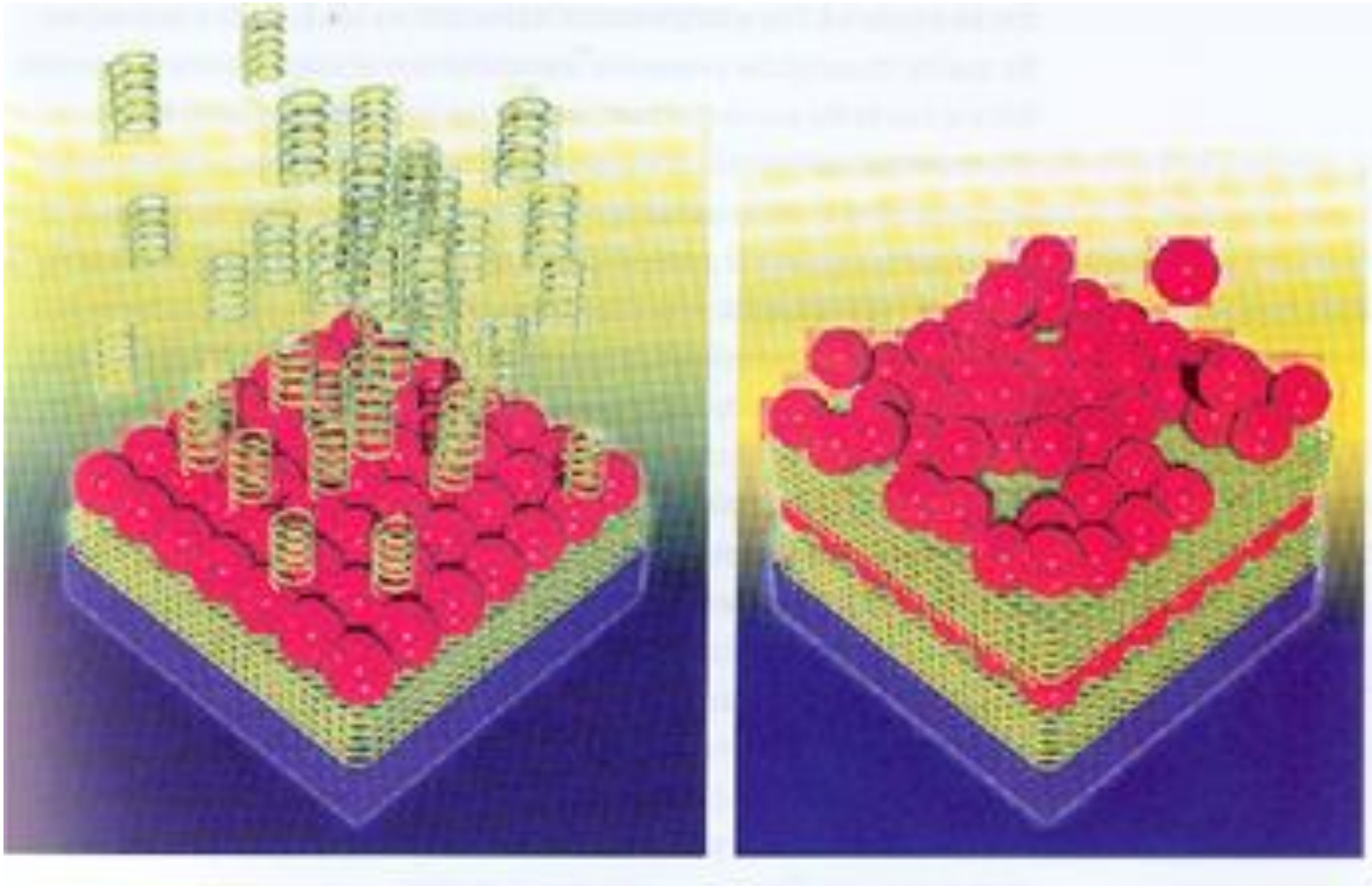
Moore's Law :

A 30% decrease in the size of printed dimensions every two years.



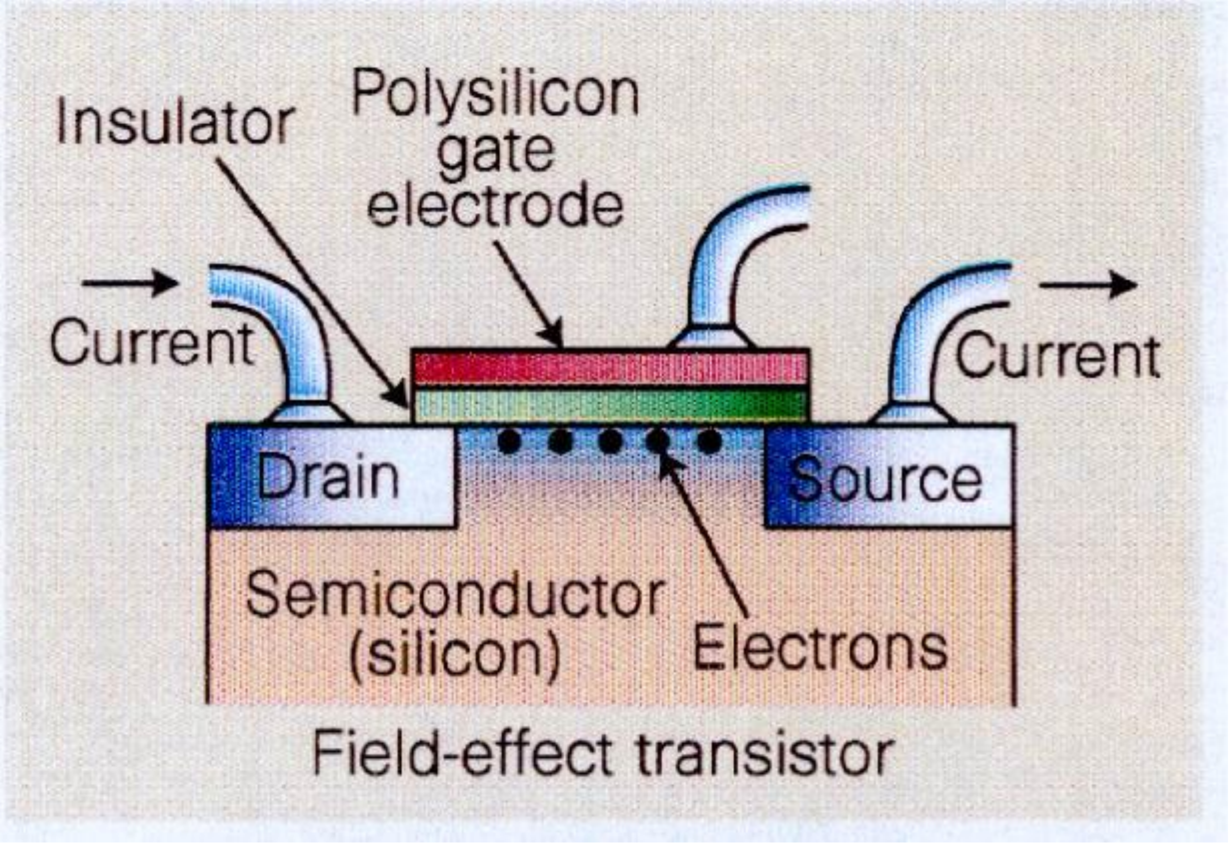
Bottom-up Nano systems & Self-Assembly

enabling of designing large molecules and nano materials



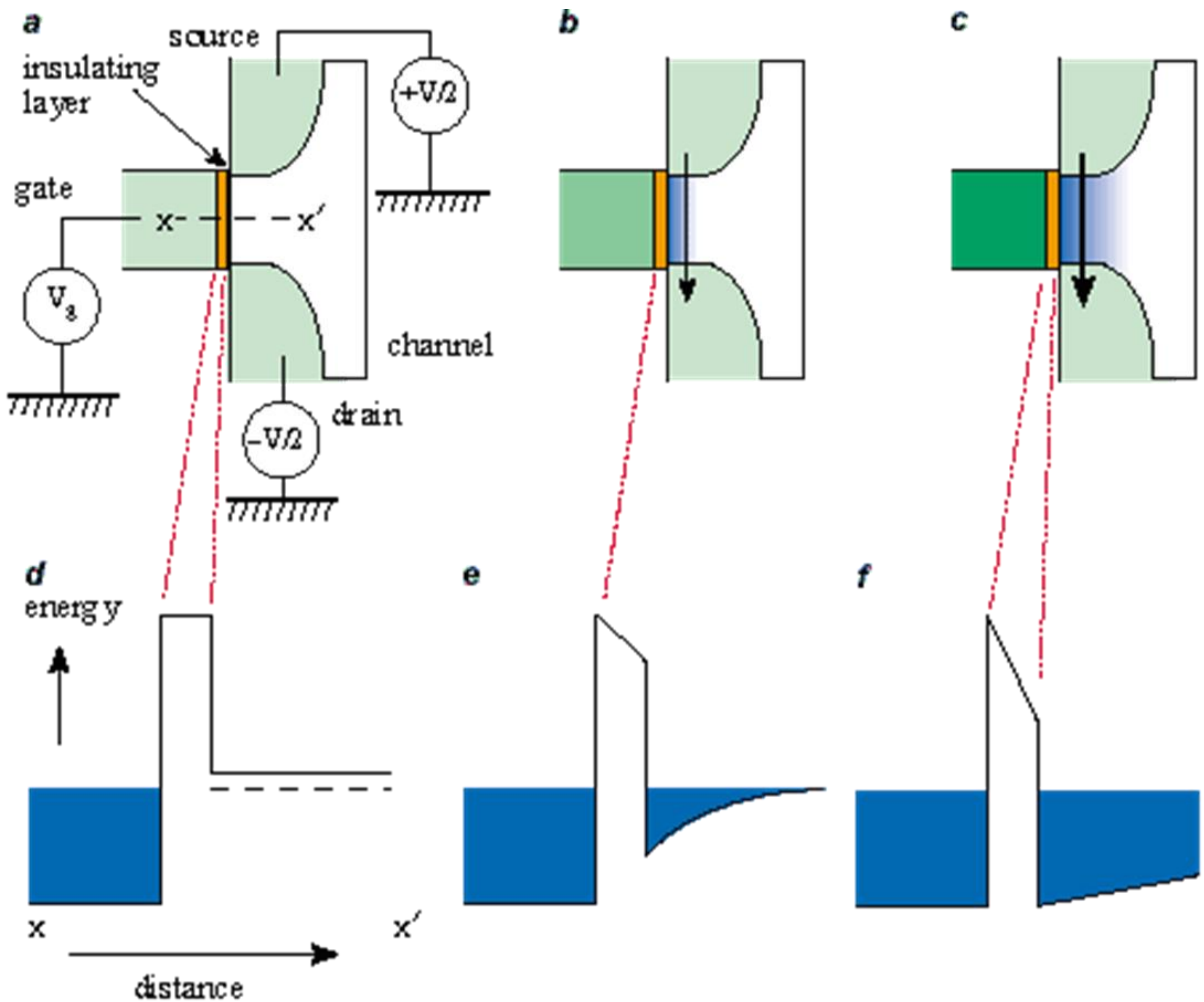
Two basic modern electronic technologies in key condensed matter physics platforms

Metal-Oxide-Feld Effect Transistor

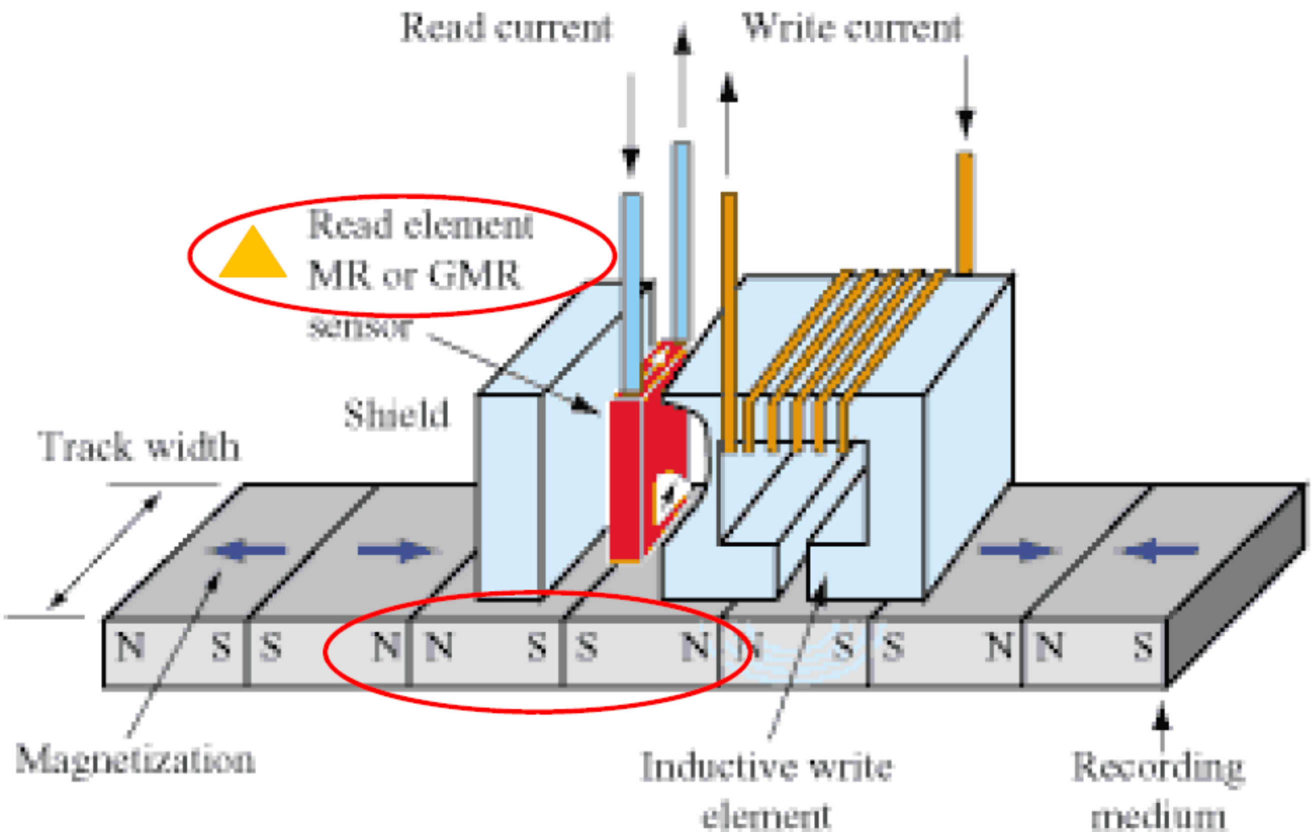


1960 Kahng and Atalla, First MOSFET
1970 First IC, 1 kbit, 750 khz microprocessor

電子科技之基礎--MOSFET
(metal-oxide-semiconductor field-effect transistor)



電子科技之基礎--磁記錄

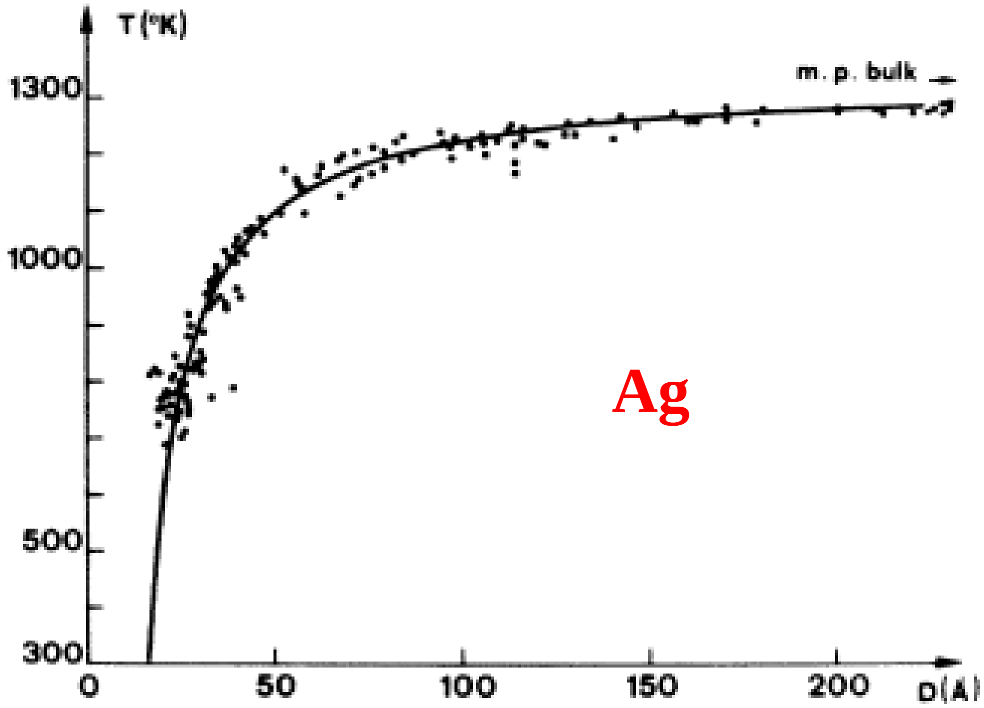


Read current
Write current
Read element
MR or GMR
sensor
Shield
Track width
N
S
S
N
N
S
S
N
N
S
S
N
N
S
Magnetization
Inductive write
element
Recording
medium

The First Lesson :

Bulk-to-nano Transition

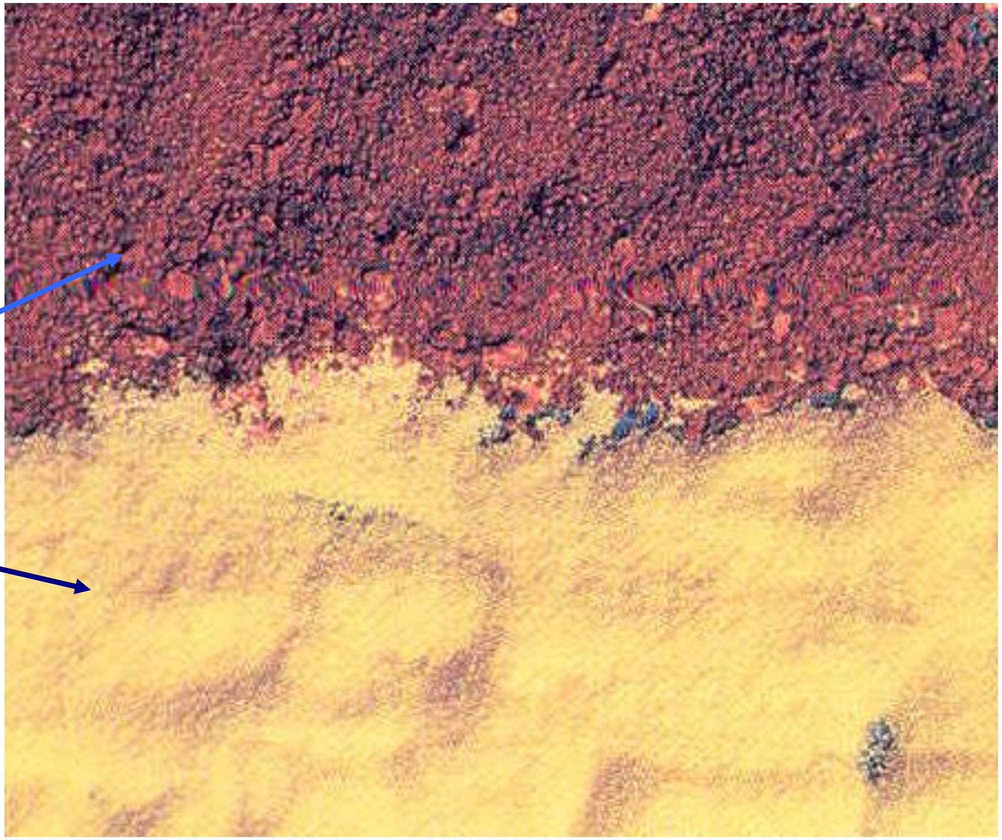
Ex: size-dependence of melting temperature



Ph. Buffat and J-P. Borel, Phys. Rev. A13, 2287 (1976)

Ex: size-dependence of color

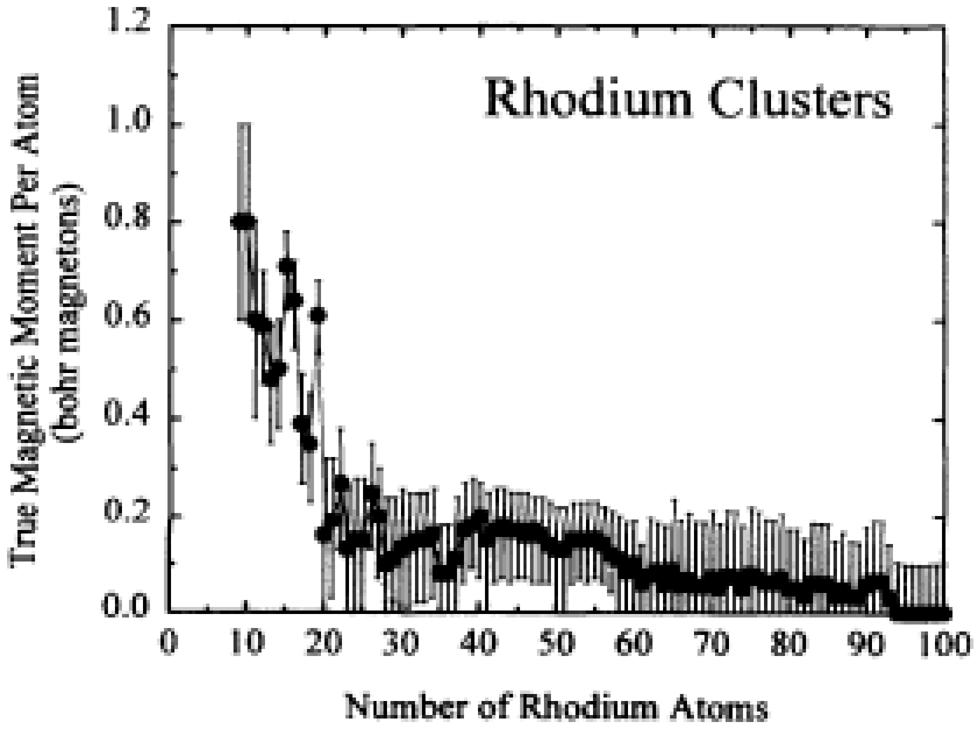
powered cadmium selenide



larger

smaller

Ex: size-dependence of magnetism



A. J. Cox et al. Phys. Rev. B49, 12295 (1994)

The Second Lesson :

- **The ability of growing the nano scale materials and structures**

- **The ability of detecting and manipulating on the nano scale.**

(I) Advance in thin film growth:

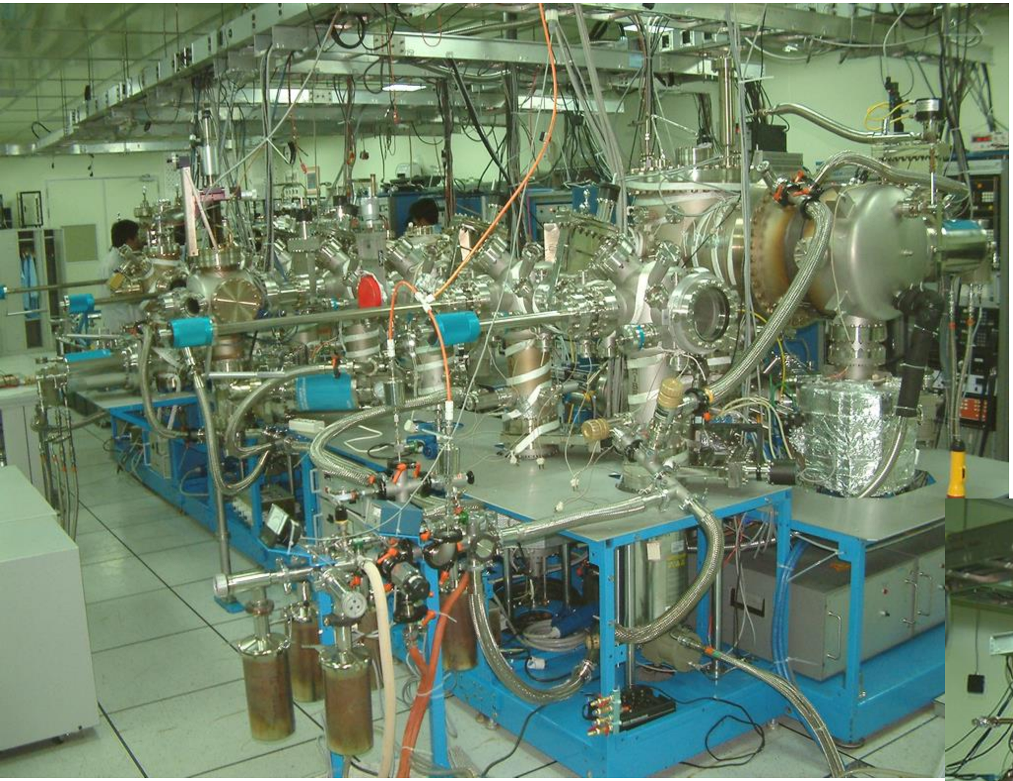
Such as Molecular Beam Epitaxy, atomic layer depostion, laser MBE, etc…

- For Nano electronics in metals, oxides, and semiconductors

(II) Detection at nano scale : STM, AFM, MFM, STEM, Cs-TEM

- In 1982, Binning, and Rohrer in IBM invented scanning tunneling microscope.
- In 1986, Binning, Quate, and Gerber invented the atomic force microscope AFM.

Integrated MBE Multi-chamber System



Now located in the Nano Technology Center, ITRI, Hsin Chu, Taiwan

For Metal, Oxide and Semiconductor Films On the Nano scale

Scanning Tunneling Microscope (STM)

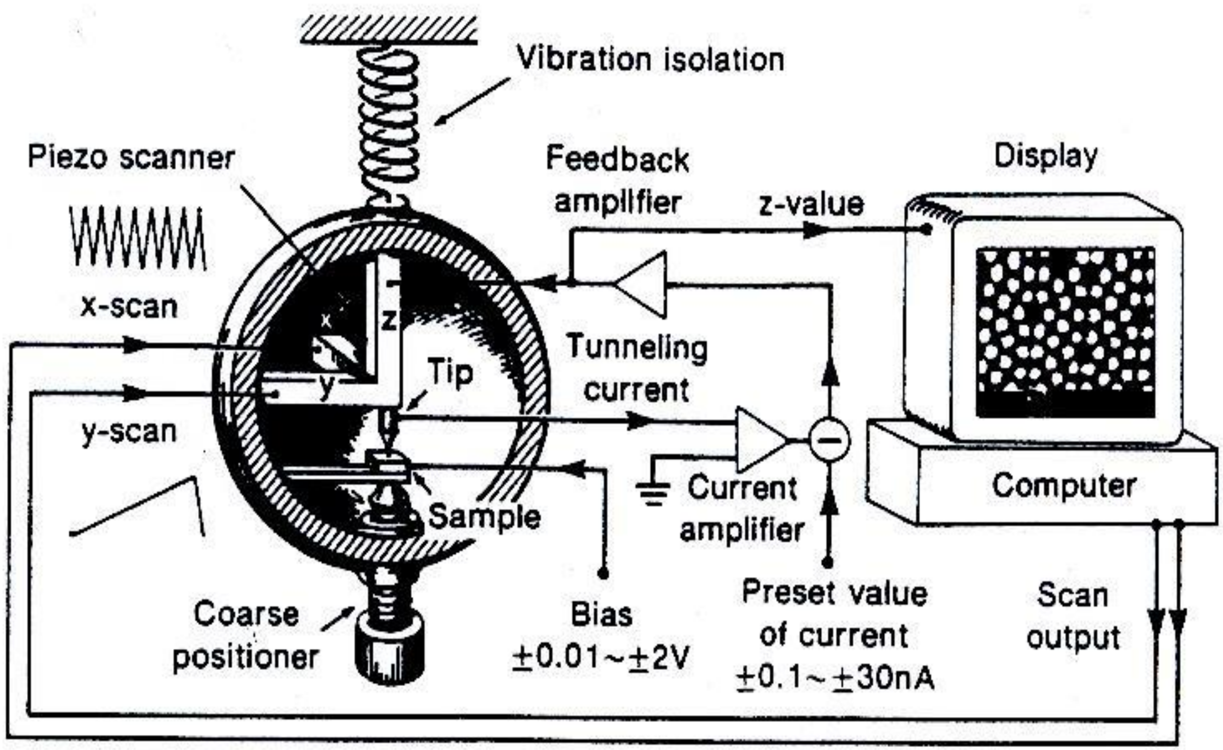
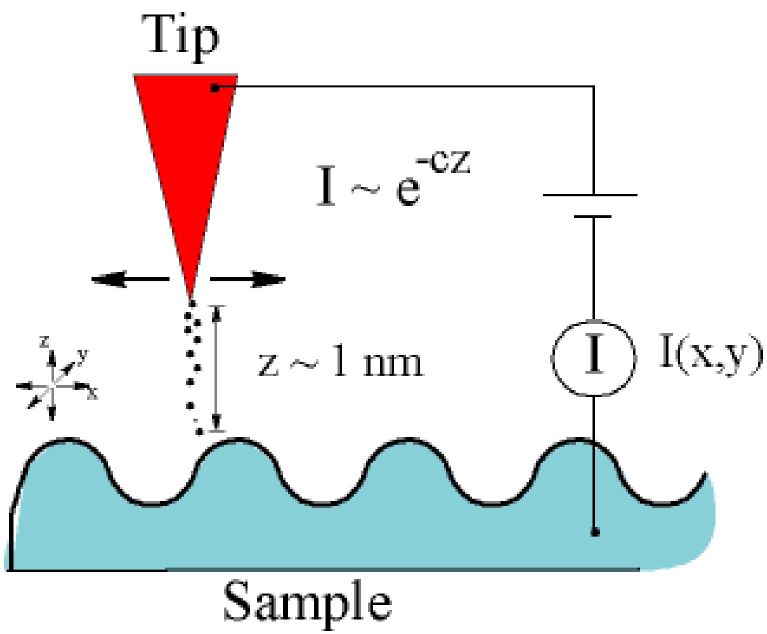
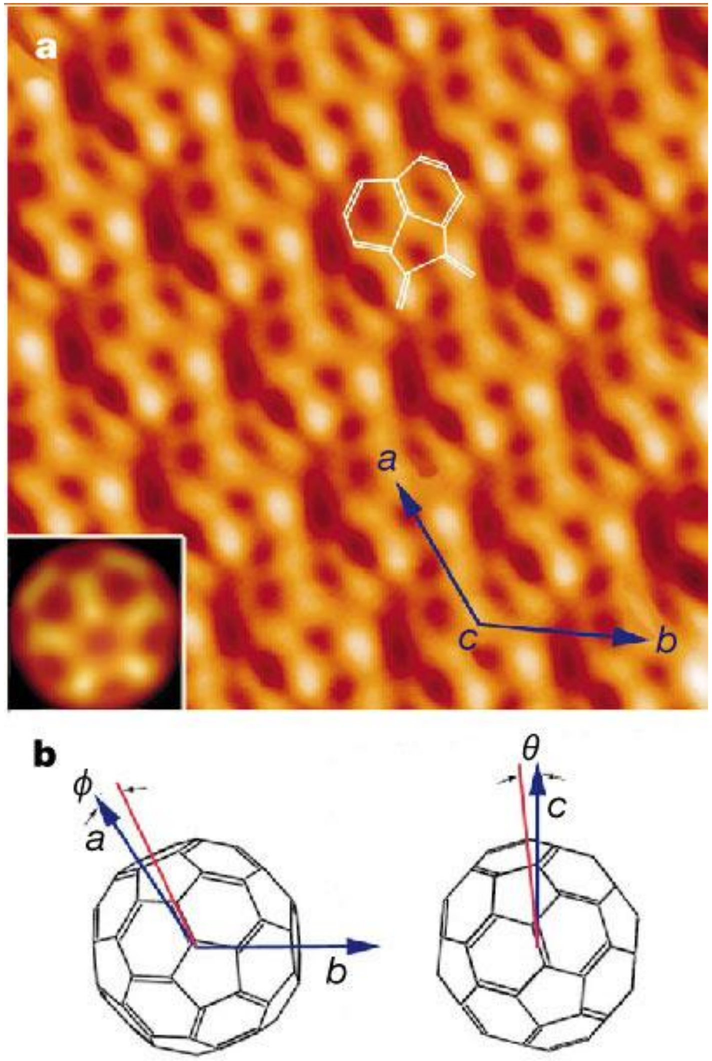


Figure 1.10 Scanning tunneling microscope. (From C. Julian Chen, *Introduction to Scanning Tunneling Microscopy*, Oxford: Oxford University Press, 1993.)

Scanning Tunneling Microscope (STM) – Physicist used to detect nano structures

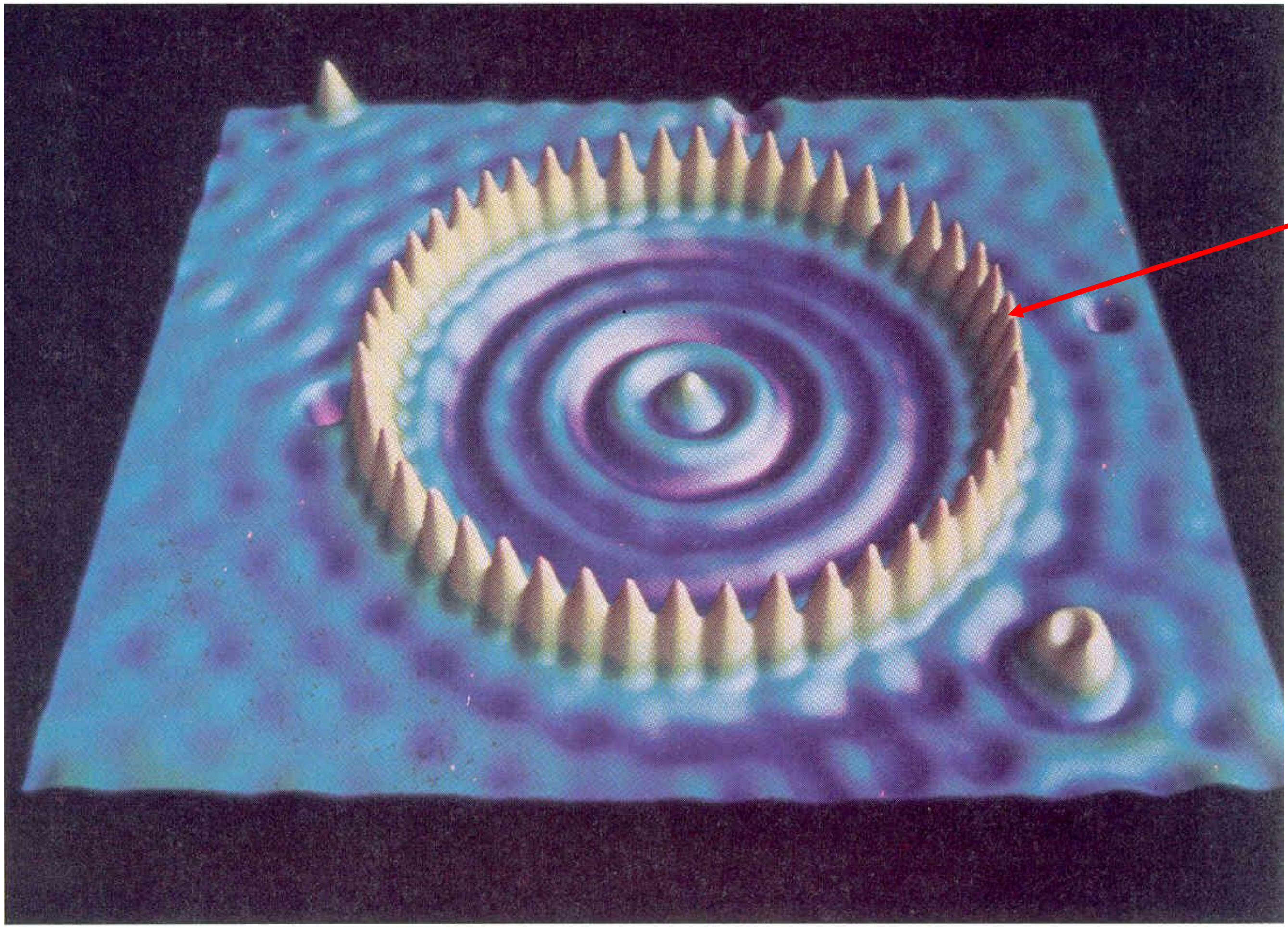


Nature 409, 304(2001)



Quantum Corral

of 7.13 nm radius, 48 Fe atoms

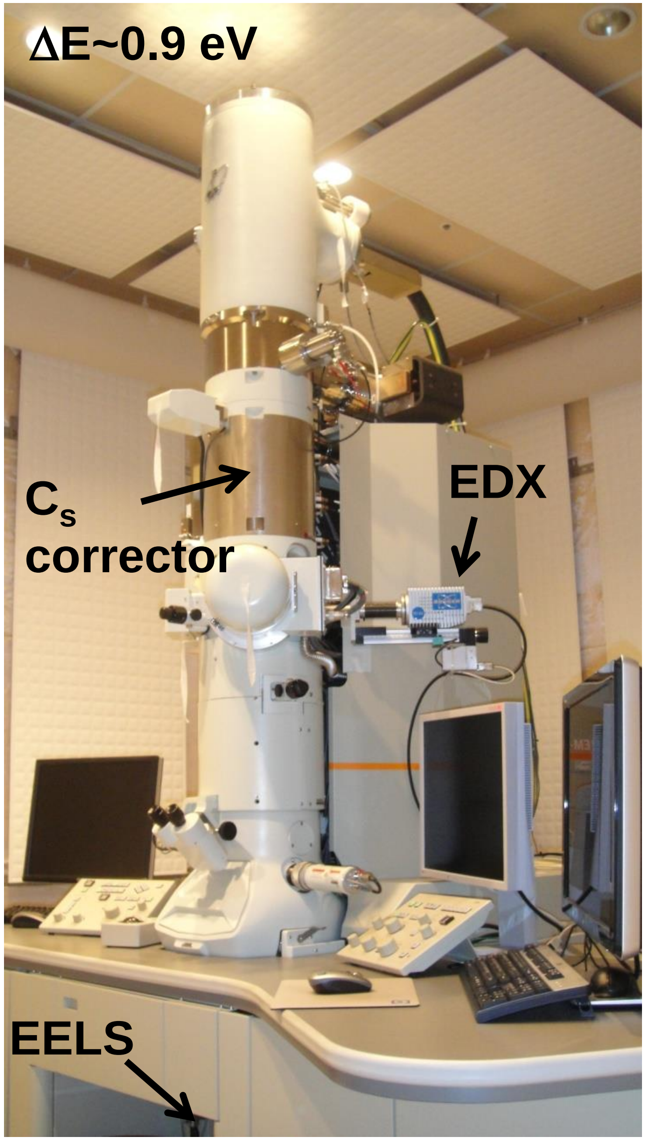


Crommue, Luts, and Eigler, Science 262, 218-220, 1993

Scanning Transmission Electron Microscope Laboratory

2-Å STEM

1-Å STEM

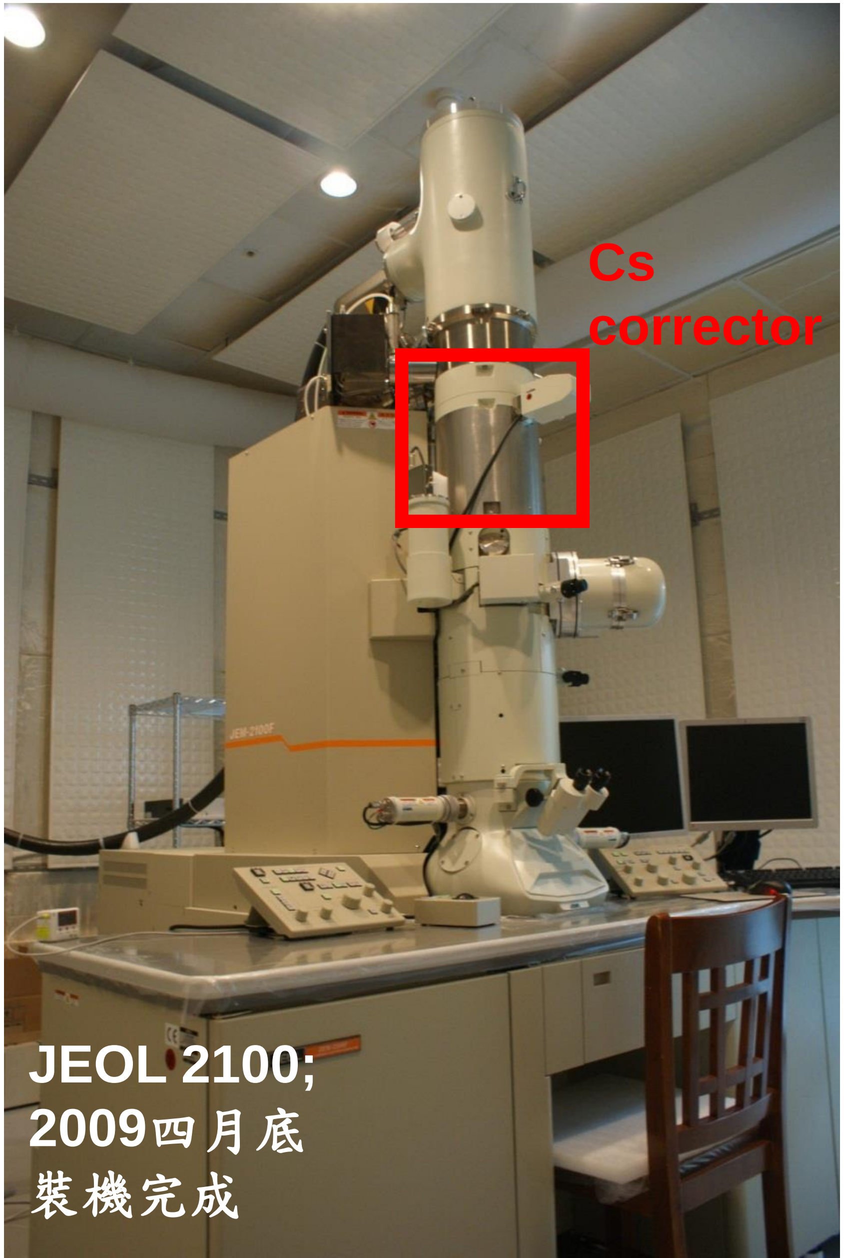


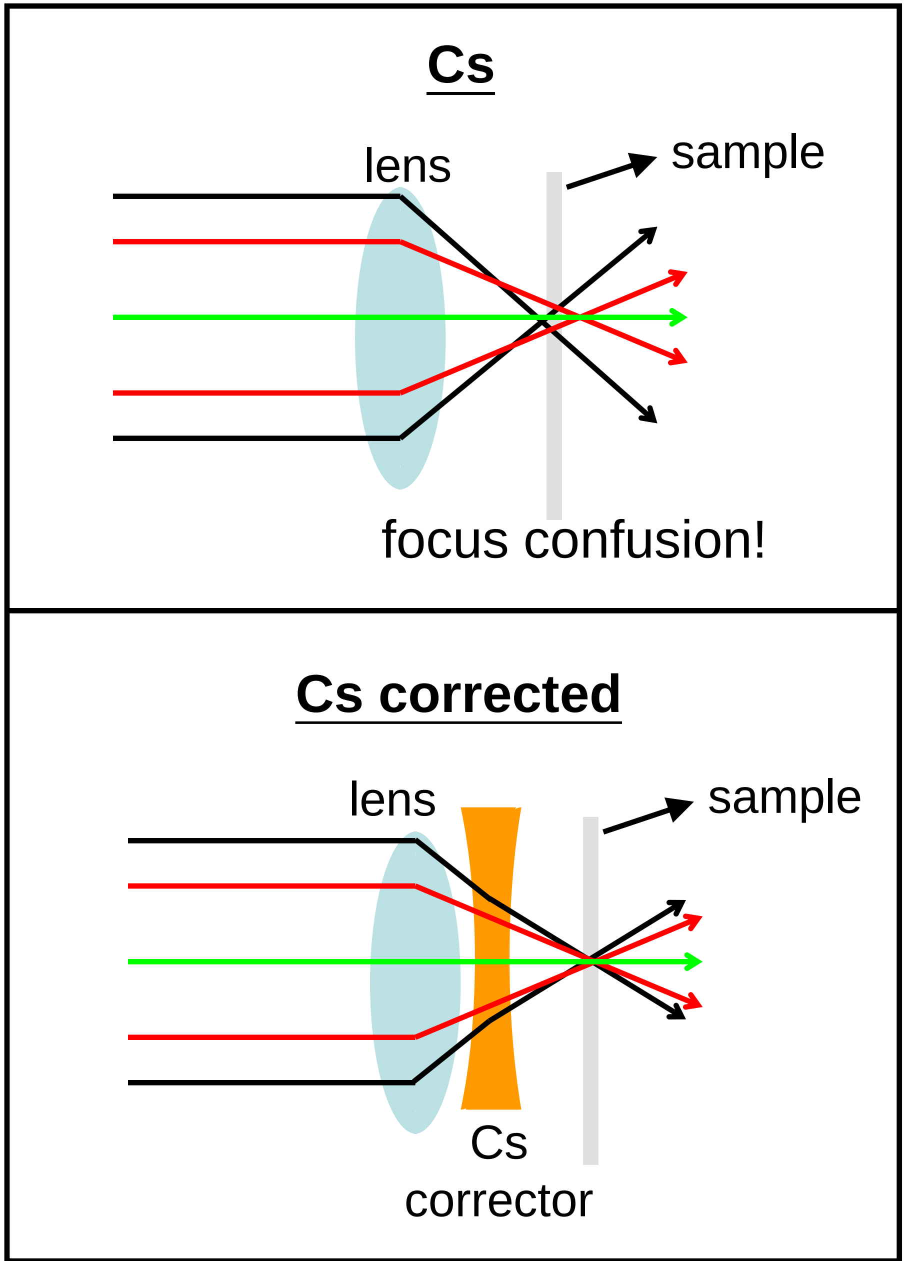
Prof. C. H. Chen and

Dr. M.-W. Chu.

Spherical Aberration Corrected (球面相差)

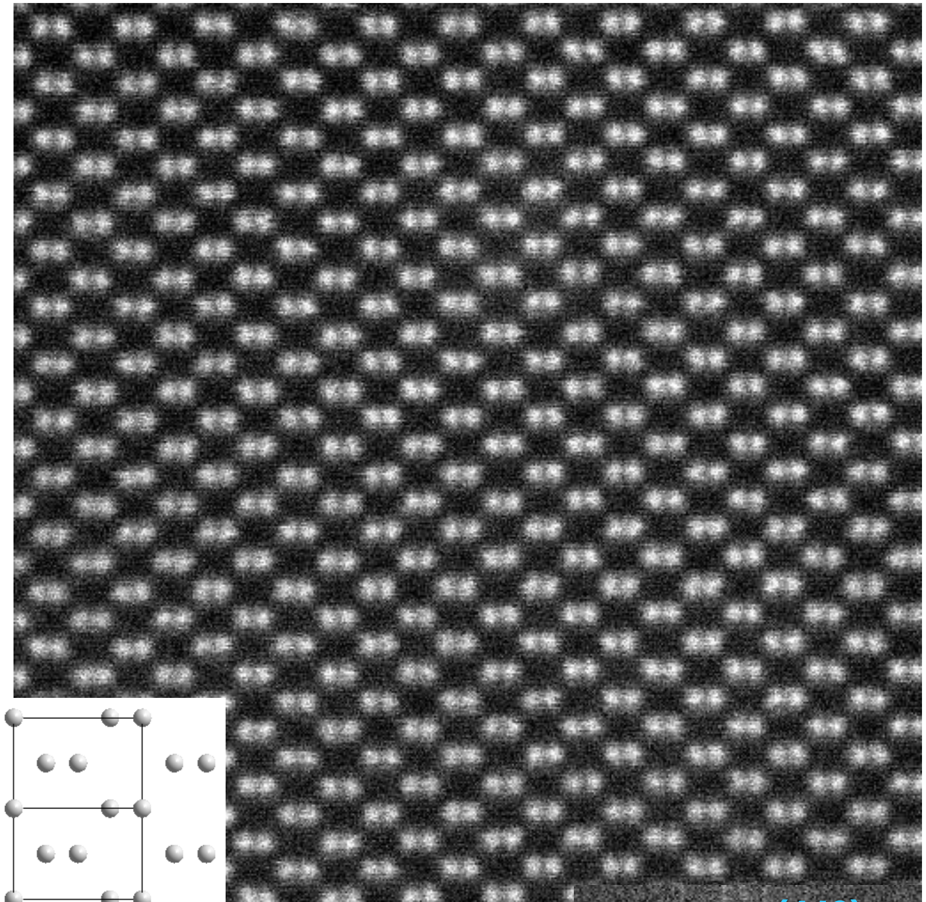
Cs-STEM by C. H. Chen at CCMS, NTU



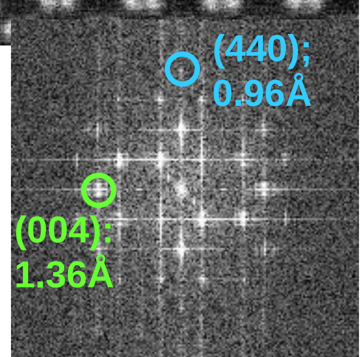


High-Angle ADF: Si dumbbell, 1.36 Å spacing

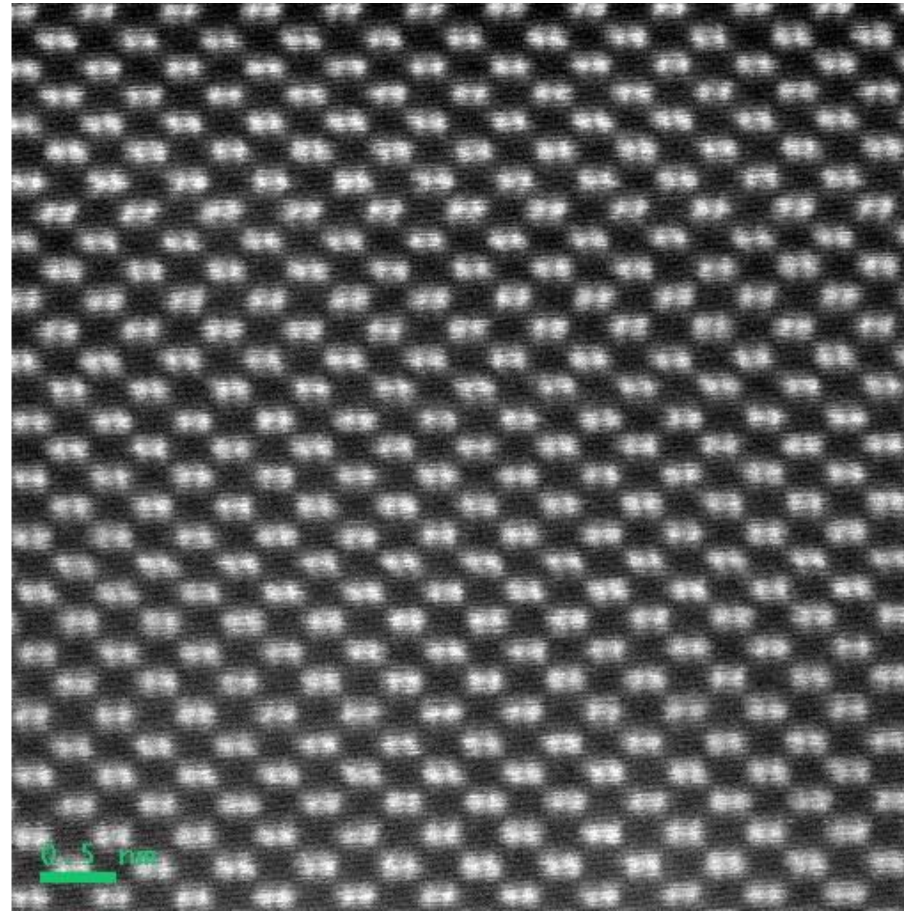
15s exposure



Si [110]

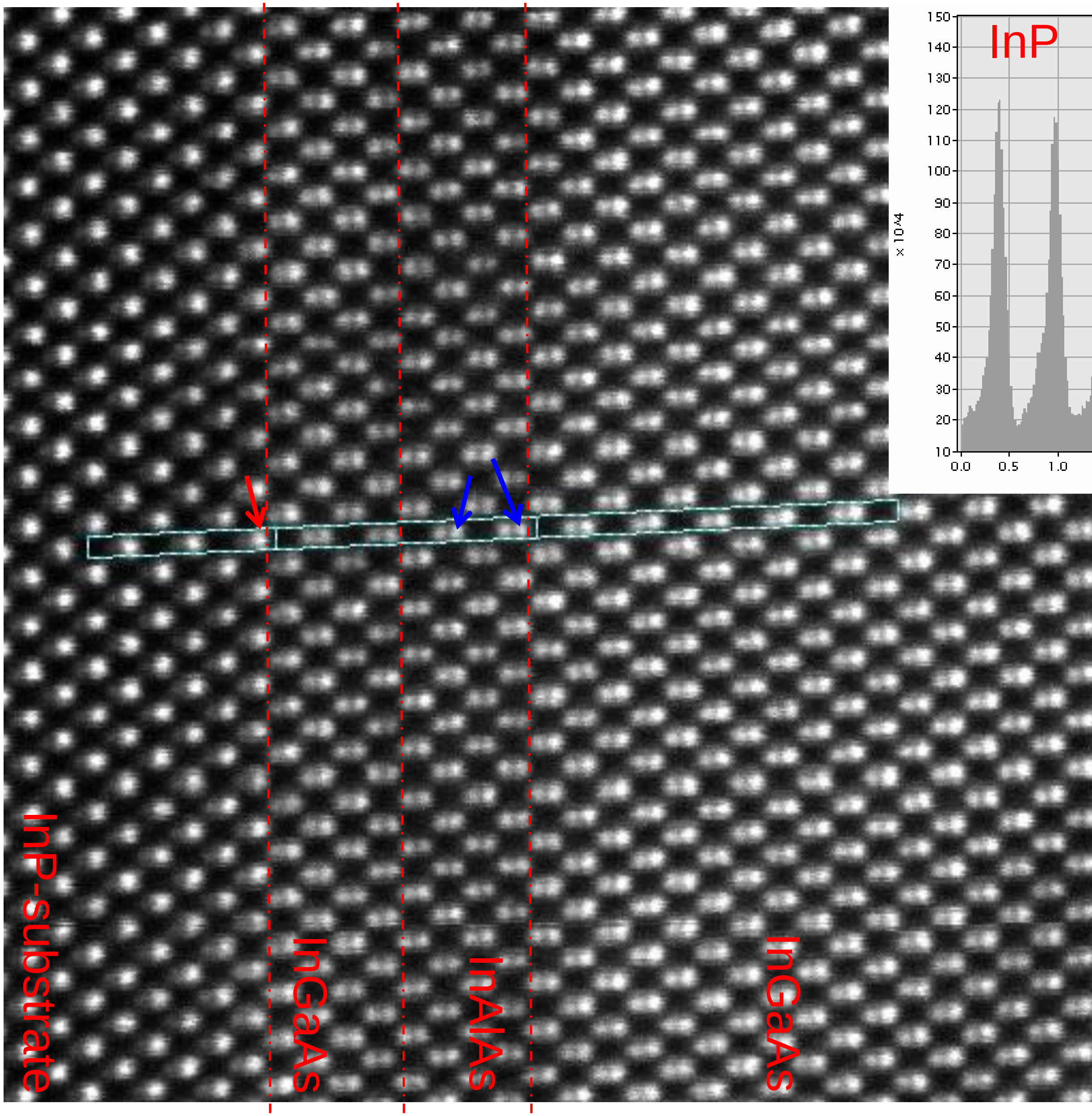


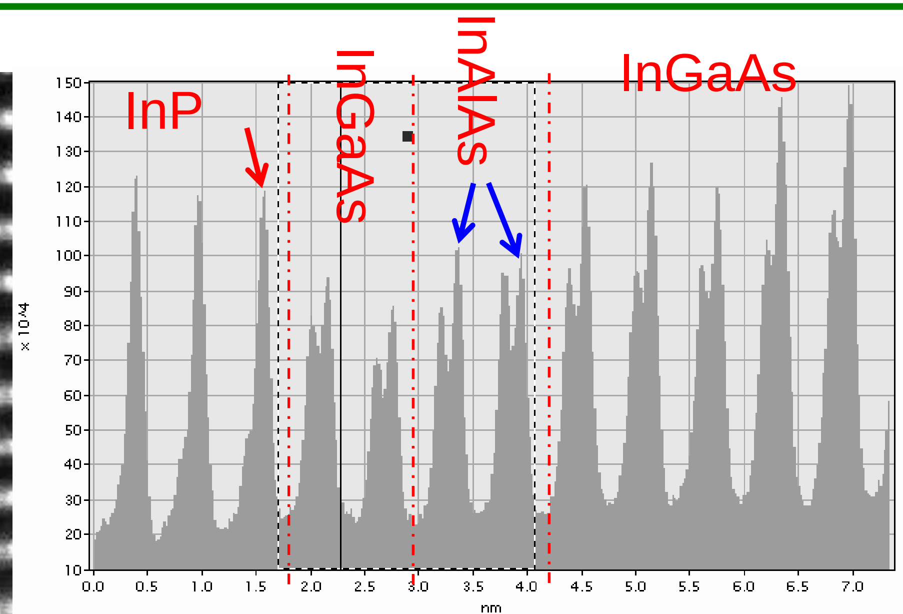
60s exposure



Drift ~1Å/min !!

InGaAs/InAlAs superlattices on InP Substrate

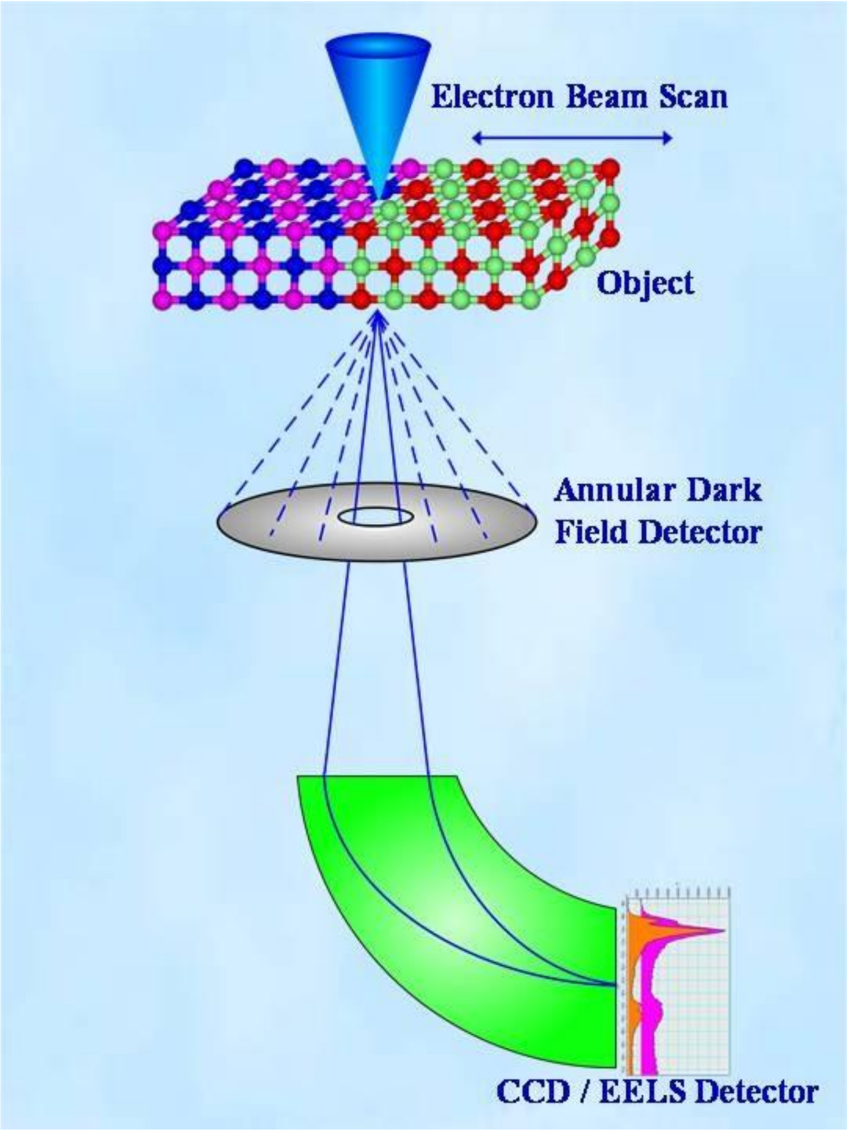


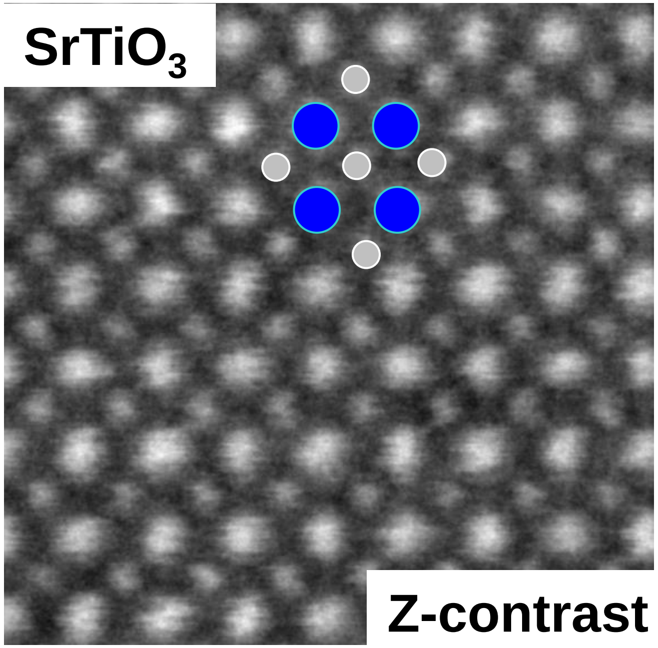


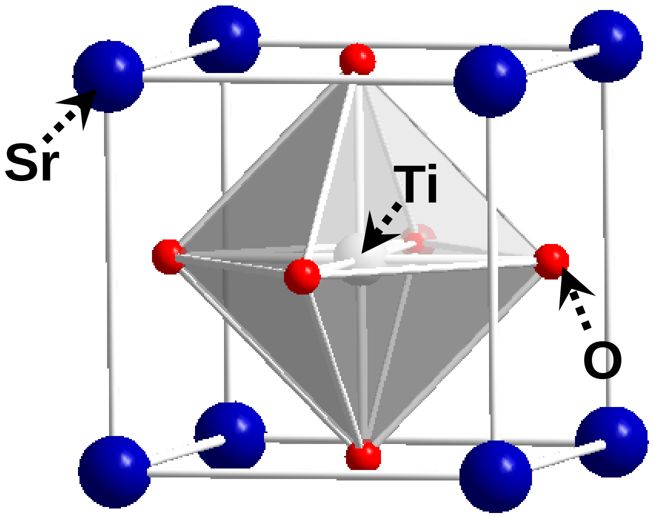
- Determining the interface location and sharpness is easy.
- The In-distribution seems to be inhomogeneous in the InAlAs layer (blue arrows).
- Note that InP substrate is In-terminated (red arrow).

Atomic Resolution STEM Imaging: Z-contrast

2-Å Electron Probe

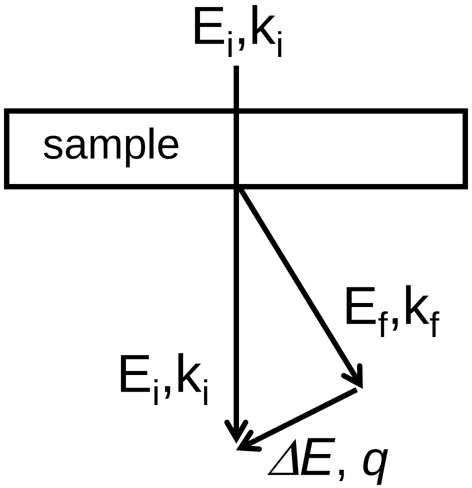






cubic; *a* = 3.905 Å

Electronic Exc.: Electron Energy-Loss Spectroscopy (EELS)



$$\Delta E = E_i - E_f$$

$$q = k_i - k_f$$

Coulomb Interaction

$$v(r) = \sum_j \frac{e^2}{|r - r_j|}$$

$$= \sum_q v_q \rho_q e^{iqr}$$

, where ρ_q the electron density operator

Inelastic Scattering (ΔE) Probability

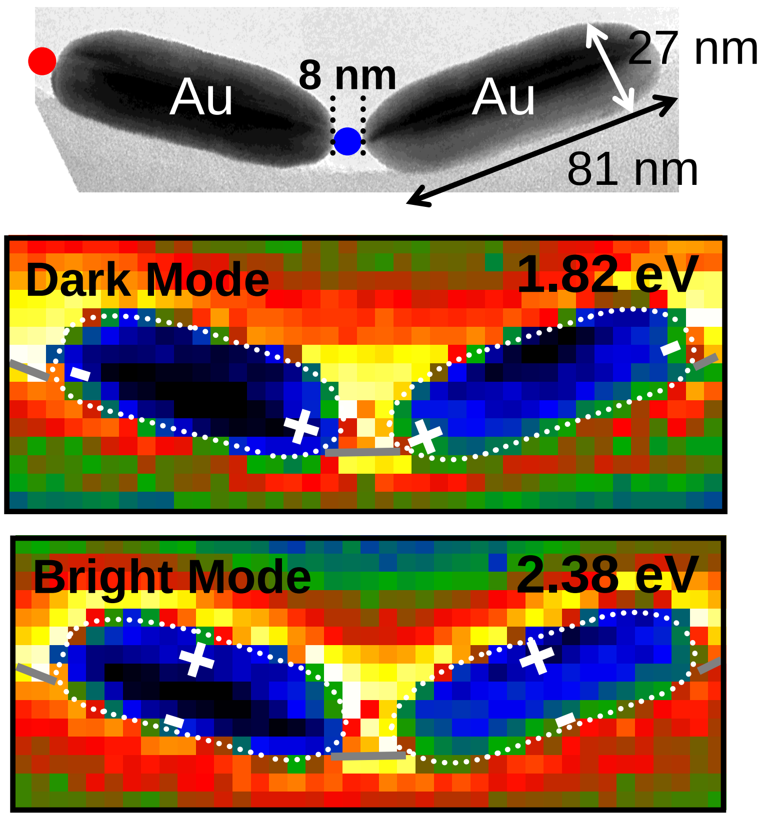
$$\frac{d^2\sigma}{d\Omega d\Delta E} \sim \sum_f \left| \langle \psi_f | v(q) | \psi_i \rangle \right|^2 \delta(E_i - E_f - \Delta E)$$

$$\sim \frac{1}{q^4} \cdot S(\omega, q) \longrightarrow \text{X-ray}$$

$$\sim \frac{1}{q^2} \cdot \mathrm{Im}\left[\frac{1}{\varepsilon(\omega, q)} \right] \longrightarrow \text{EELS}$$

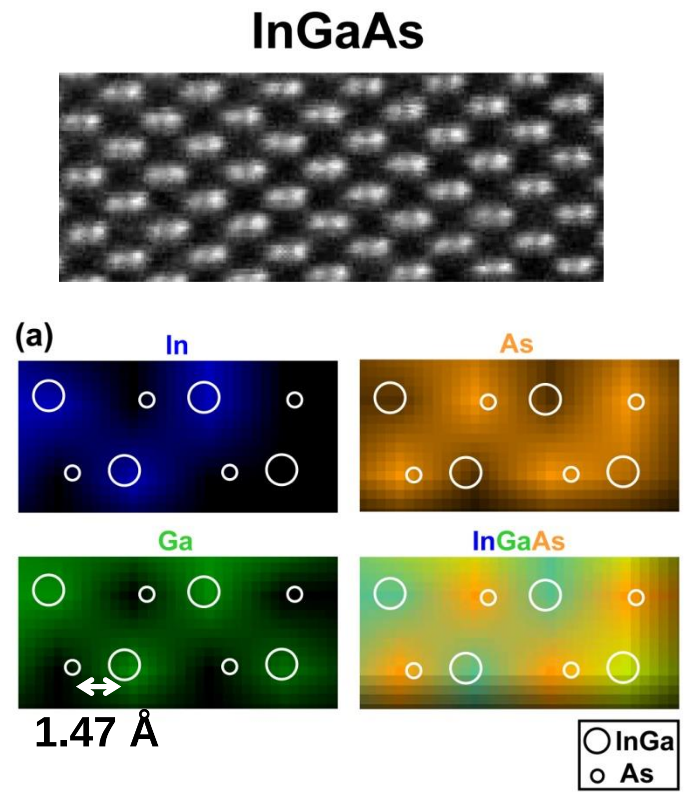
Spectral Imaging at Ultimate Spatial Resolution

Plasmonic Mapping: STEM-EELS (2-Å Probe)



M.-W. Chu *et al.*, Nano Lett. **9**, 399 (2009).

Chemical Mapping: STEM-EDX (1-Å Probe)



M.-W. Chu *et al.*, Phys. Rev. Lett. **104**, 196101 (2010).

The Third Lesson:

The importance of Quantum Physics

The cause for variation of scaling

- Influence of Boundary
  - --Increase of proportion of boundaries
  - --Existence of surface / edge modes
  - --Geometrical reconstruction

- Decrease of the number of particles
  decrease of confinement , increase of purturbation

- Different scaling for different physical entity

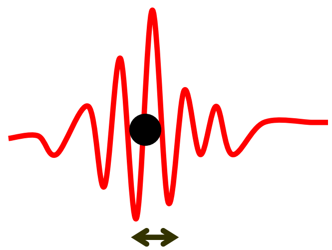
Quantum Effect:

=> Most likely to have new breakthough !

The connection of materials wave with mechanics

h = Planck constant
$(6.626\times10^{-34}$ joule-sec)

DeBroglie:
$\lambda = h/p$



λ

Einstein:
$E=h\nu=p^2/2m$

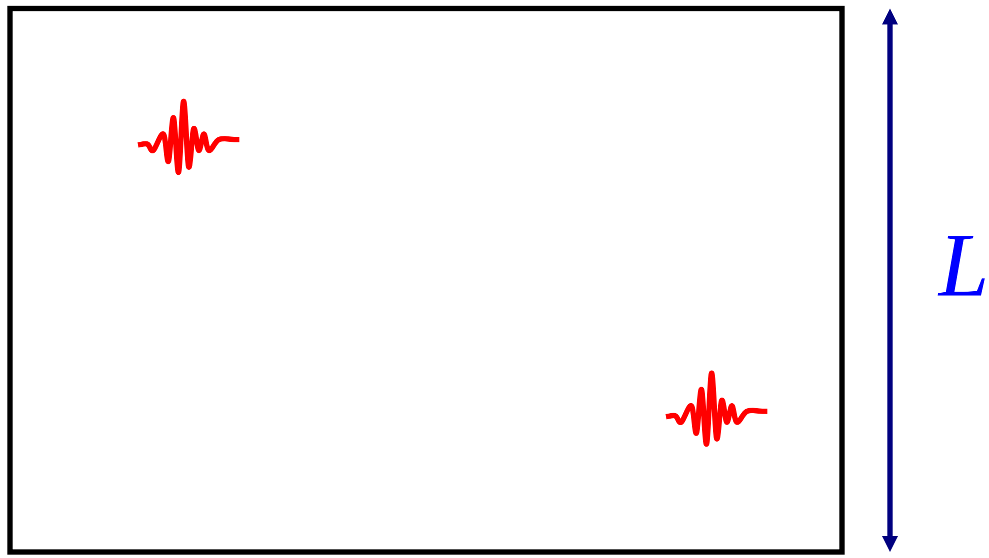
Wave length

Free electrons	$\lambda_{th}(300K) = 6.2nm$
Semiconductors	$10nm \le \lambda \le 100nm)$
Atoms	$(300K) \le 0.2nm$

Bulk Limit ⇔ Nano Limit

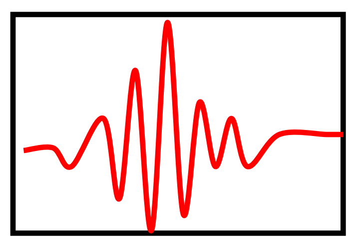
Bulk materials

$\lambda \ll L$



Nano

$\lambda \sim L$

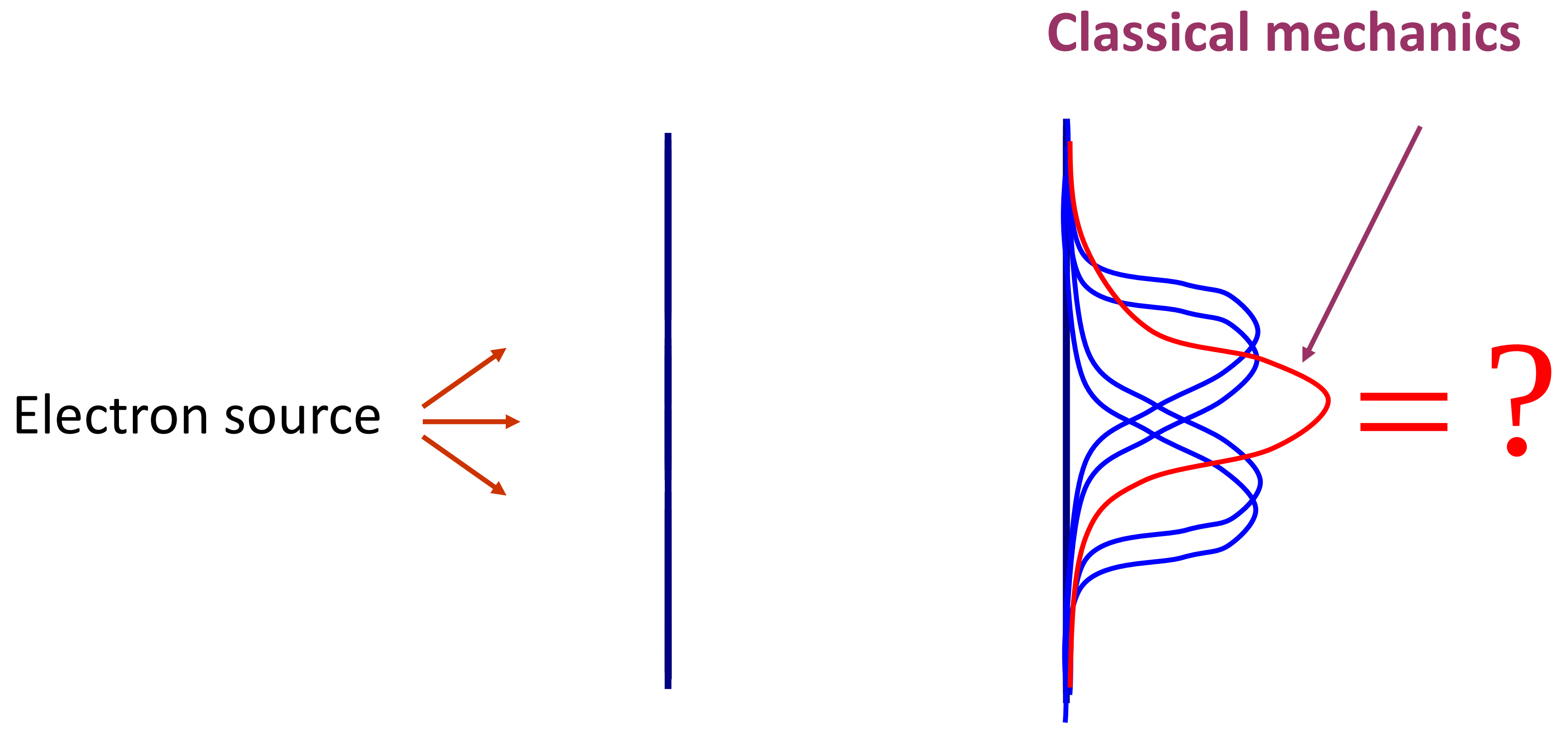


Major Qauntum Effect at the nano scale

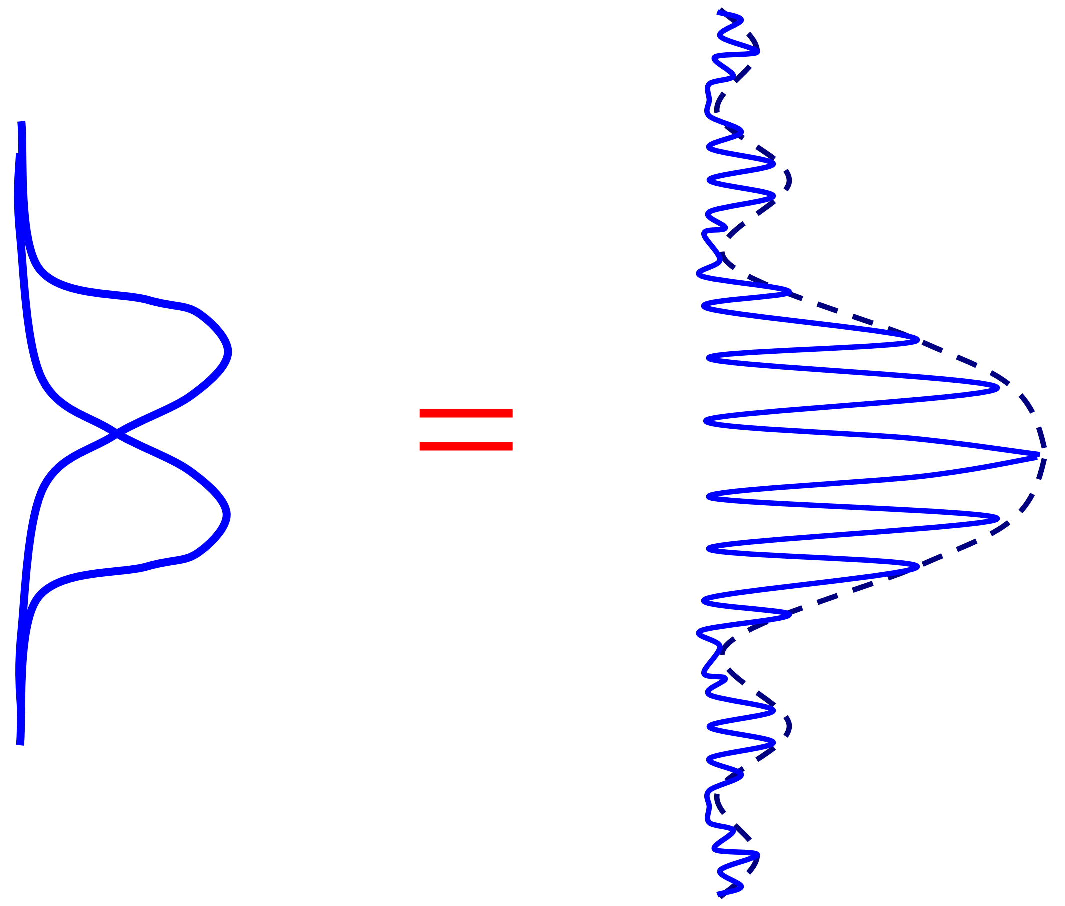
- Interference
- Quantization
- Tunneling
- Quantum Spin

(I) Interference

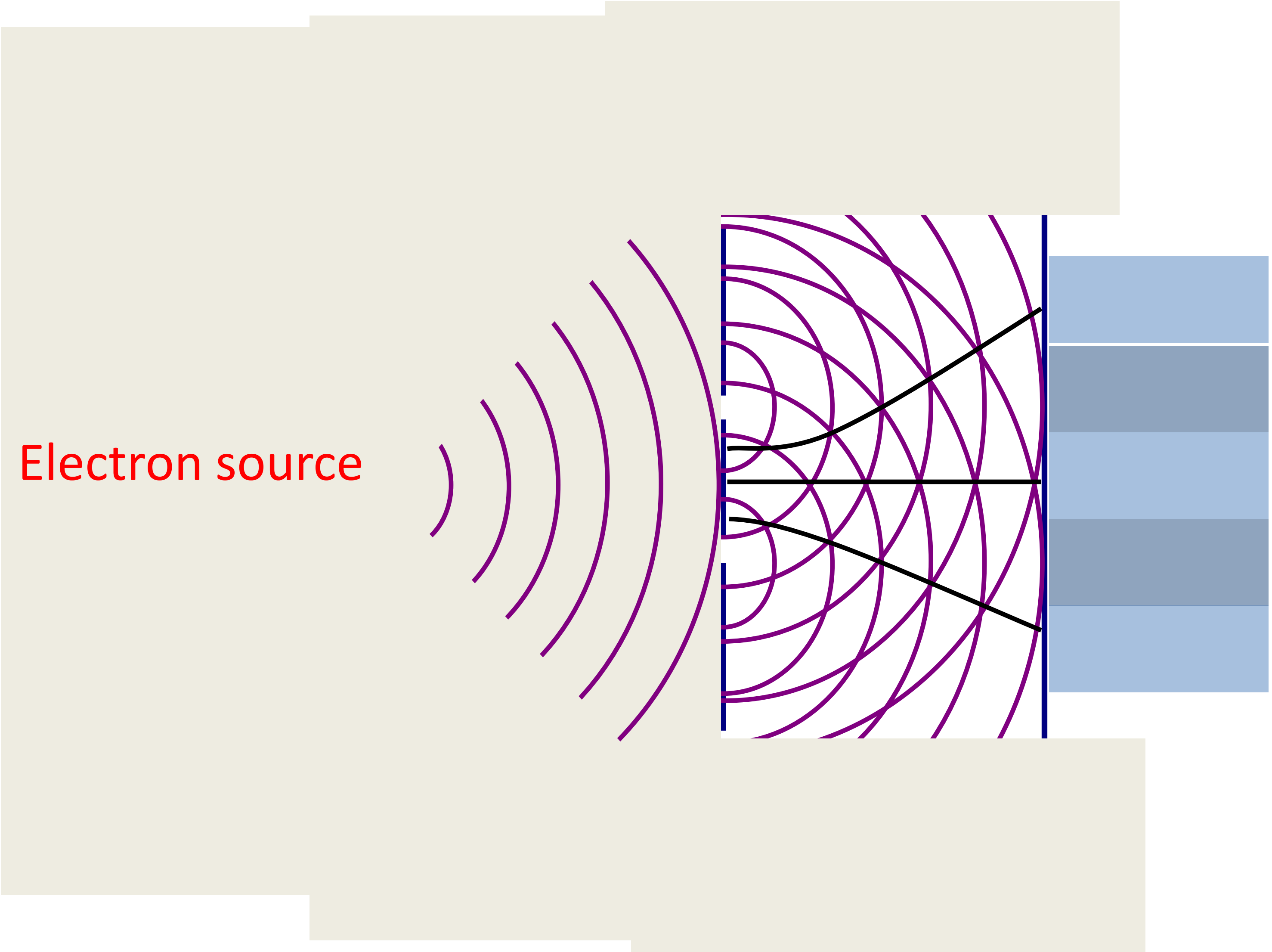
The wonder of electron in waves

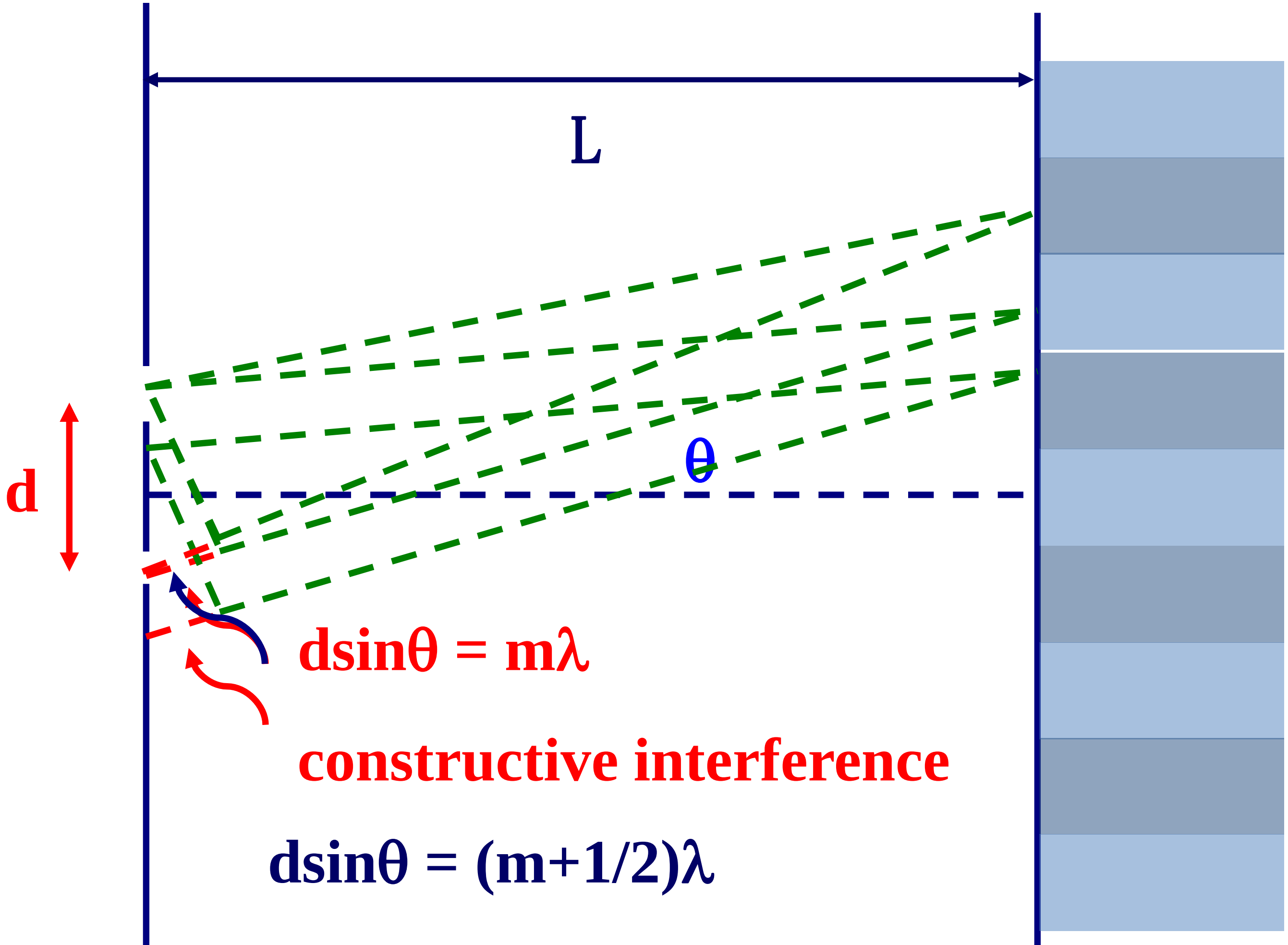


The wave property of electrons



Double Slit Interference of Electrons





$$\Delta y = \frac{L}{d}\lambda$$

dsinθ = mλ

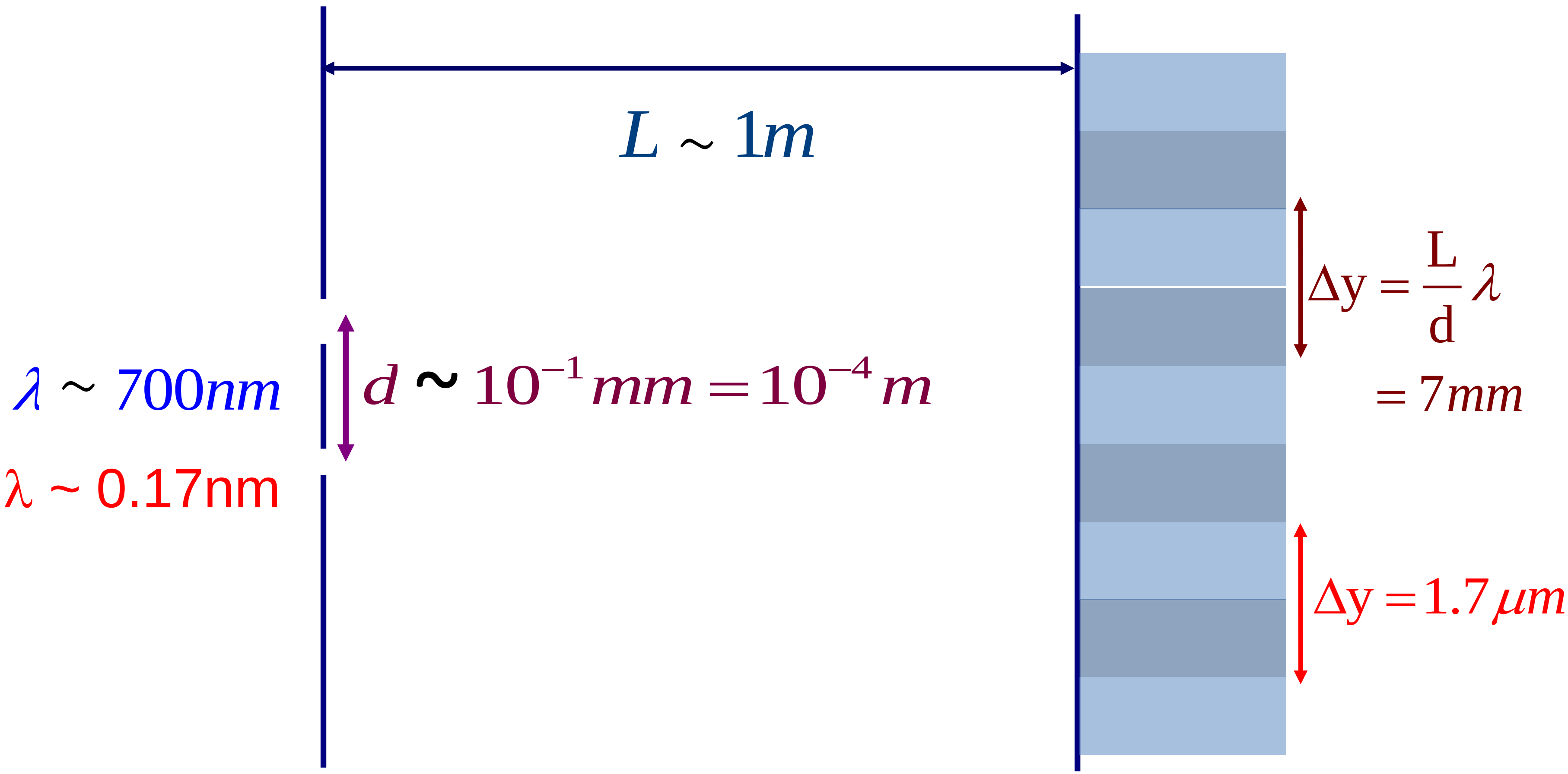
constructive interference

dsinθ = (m+1/2)λ

distructive interference

$$d\frac{\Delta y}{L} = \lambda$$

~


$L \sim 1m$
$\Delta y = \frac{L}{d}\lambda$
$= 7mm$
$\lambda \sim 700nm$
$d \sim 10^{-1}mm = 10^{-4}m$
$\lambda \sim 0.17nm$
$\Delta y = 1.7\mu m$